SiZ918DT

Vishay Siliconix

Dual N-Channel 30 V (D-S) MOSFETs

PRODUCT SUMMARY				
	V_{DS} (V)	$R_{DS(on)}$ (Ω) (Max.)	I_D (A)	Q_g (Typ.)
Channel-1	30	0.0120 at V_{GS} = 10 V	16[a]	6.8 nC
		0.0145 at V_{GS} = 4.5 V	16[a]	
Channel-2	30	0.0037 at V_{GS} = 10 V	28[a]	32 nC
		0.0045 at V_{GS} = 4.5 V	28[a]	

FEATURES

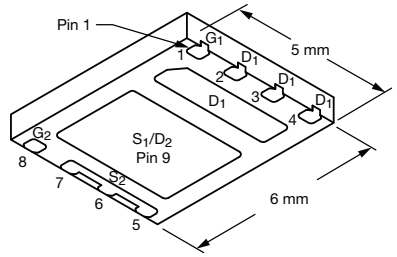
- TrenchFET® Power MOSFETs
- 100 % R_g and UIS Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

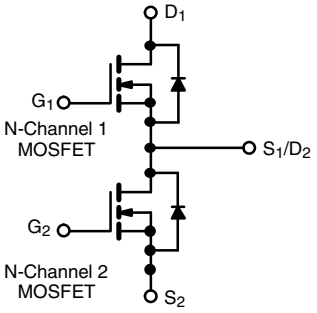
Pb-free
RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Notebook System Power
- POL
- Synchronous Buck Converter

PowerPAIR® 6 x 5





Ordering Information: SiZ918DT-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)					
Parameter		**Symbol**	**Channel-1**	**Channel-2**	**Unit**
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	16[a]	28[a]	A
	T_C = 70 °C		16[a]	28[a]	
	T_A = 25 °C		14.3[b, c]	26[a, b, c]	
	T_A = 70 °C		11.4[b, c]	21[a, b, c]	
Pulsed Drain Current (t = 300 µs)		I_{DM}	50	110	
Continuous Source Drain Diode Current	T_C = 25 °C	I_S	16[a]	28[a]	
	T_A = 25 °C		3.4[b, c]	4.3[b, c]	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	18	35	
Single Pulse Avalanche Energy		E_{AS}	16	61	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	29	100	W
	T_C = 70 °C		18	64	
	T_A = 25 °C		4.2[b, c]	5.2[b, c]	
	T_A = 70 °C		2.7[b, c]	3.3[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature)[d, e]			260		

THERMAL RESISTANCE RATINGS							
			Channel-1		Channel-2		
Parameter		**Symbol**	**Typ.**	**Max.**	**Typ.**	**Max.**	**Unit**
Maximum Junction-to-Ambient[b, f]	t ≤ 10 s	R_{thJA}	24	30	19	24	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	3.4	4.3	1	1.25	

Notes:
a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. See solder profile (www.vishay.com/doc?73257). The PowerPAIR is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
f. Maximum under steady state conditions is 65 °C/W for channel-1 and 55 °C/W for channel-2.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)							
Parameter	**Symbol**	**Test Conditions**		**Min.**	**Typ.**	**Max.**	**Unit**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	Ch-1	30			V
		V_{GS} = 0 V, I_D = 250 µA	Ch-2	30			
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA	Ch-1		33		mV/°C
		I_D = 250 µA	Ch-2		37		
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I_D = 250 µA	Ch-1		- 5		
		I_D = 250 µA	Ch-2		- 7.5		
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	Ch-1	1		2.2	V
		V_{DS} = V_{GS}, I_D = 250 µA	Ch-2	1.2		2.2	
Gate Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	Ch-1			± 100	nA
			Ch-2			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V	Ch-1			1	µA
		V_{DS} = 30 V, V_{GS} = 0 V	Ch-2			1	
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 55 °C	Ch-1			5	
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 55 °C	Ch-2			5	
On-State Drain Current[b]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	Ch-1	20			A
		$V_{DS} \geq$ 5 V, V_{GS} = 10 V	Ch-2	20			
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 13.8 A	Ch-1		0.0100	0.0120	Ω
		V_{GS} = 10 V, I_D = 20 A	Ch-2		0.0030	0.0037	
		V_{GS} = 4.5 V, I_D = 12.6 A	Ch-1		0.0120	0.0145	
		V_{GS} = 4.5 V, I_D = 20 A	Ch-2		0.0035	0.0045	
Forward Transconductance[b]	g_{fs}	V_{DS} = 10 V, I_D = 13.8 A	Ch-1		47		S
		V_{DS} = 10 V, I_D = 20 A	Ch-2		116		
Dynamic[a]							
Input Capacitance	C_{iss}	Channel-1 V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz	Ch-1		790		pF
			Ch-2		3830		
Output Capacitance	C_{oss}		Ch-1		190		
		Channel-2 V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz	Ch-2		670		
Reverse Transfer Capacitance	C_{rss}		Ch-1		76		
			Ch-2		315		
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 13.8 A	Ch-1		14	21	nC
		V_{DS} = 15 V, V_{GS} = 10 V, I_D = 20 A	Ch-2		67.3	105	
		Channel-1 V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 13.8 A	Ch-1		6.8	11	
			Ch-2		32	48	
Gate-Source Charge	Q_{gs}	Channel-2 V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 20 A	Ch-1		2.6		
			Ch-2		10.8		
Gate-Drain Charge	Q_{gd}		Ch-1		1.9		
			Ch-2		9.3		
Gate Resistance	R_g	f = 1 MHz	Ch-1	0.4	2	4	Ω
			Ch-2	0.2	1.1	2.2	

Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

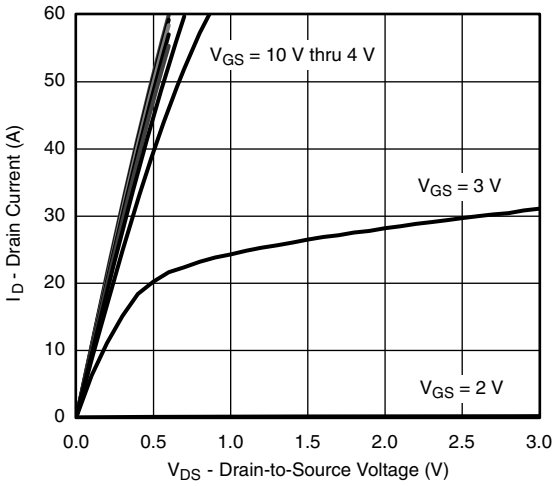
For more information please contact: pmostechsupport@vishay.com
Document Number: 63783
S12-0543 Rev. A, 12-Mar-12

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)							
Parameter	**Symbol**	**Test Conditions**		**Min.**	**Typ.**	**Max.**	**Unit**
Dynamic[a]							
Turn-On Delay Time	$t_{d(on)}$	Channel-1 V_{DD} = 15 V, R_L = 1.5 Ω $I_D \cong$ 10 A, V_{GEN} = 4.5 V, R_g = 1 Ω	Ch-1		15	30	ns
			Ch-2		30	60	
Rise Time	t_r		Ch-1		12	20	
			Ch-2		33	65	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 V_{DD} = 15 V, R_L = 1.5 Ω $I_D \cong$ 10 A, V_{GEN} = 4.5 V, R_g = 1 Ω	Ch-1		20	40	
			Ch-2		40	80	
Fall Time	t_f		Ch-1		10	20	
			Ch-2		12	25	
Turn-On Delay Time	$t_{d(on)}$	Channel-1 V_{DD} = 15 V, R_L = 1.5 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	Ch-1		10	20	
			Ch-2		15	30	
Rise Time	t_r		Ch-1		12	20	
			Ch-2		22	25	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 V_{DD} = 15 V, R_L = 1.5 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	Ch-1		20	40	
			Ch-2		40	80	
Fall Time	t_f		Ch-1		10	20	
			Ch-2		10	20	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C	Ch-1			16	A
			Ch-2			28	
Pulse Diode Forward Current[a]	I_{SM}		Ch-1			50	
			Ch-2			110	
Body Diode Voltage	V_{SD}	I_S = 10 A, V_{GS} = 0 V	Ch-1		0.85	1.2	V
		I_S = 10 A, V_{GS} = 0 V	Ch-2		0.8	1.2	
Body Diode Reverse Recovery Time	t_{rr}	Channel-1 I_F = 10 A, dI/dt = 100 A/µs, T_J = 25 °C	Ch-1		20	40	ns
			Ch-2		30	60	
Body Diode Reverse Recovery Charge	Q_{rr}		Ch-1		10	20	nC
			Ch-2		21	40	
Reverse Recovery Fall Time	t_a	Channel-2 I_F = 10 A, dI/dt = 100 A/µs, T_J = 25 °C	Ch-1		11		ns
			Ch-2		17		
Reverse Recovery Rise Time	t_b		Ch-1		9		
			Ch-2		13		

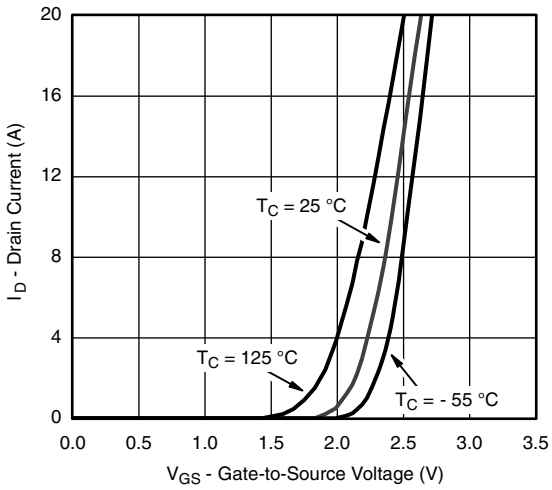
Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

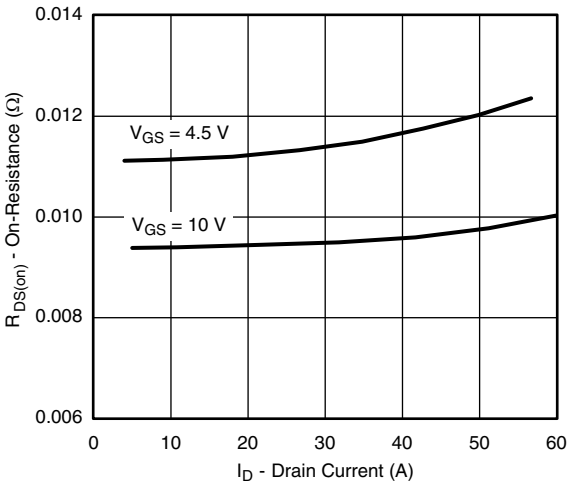
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



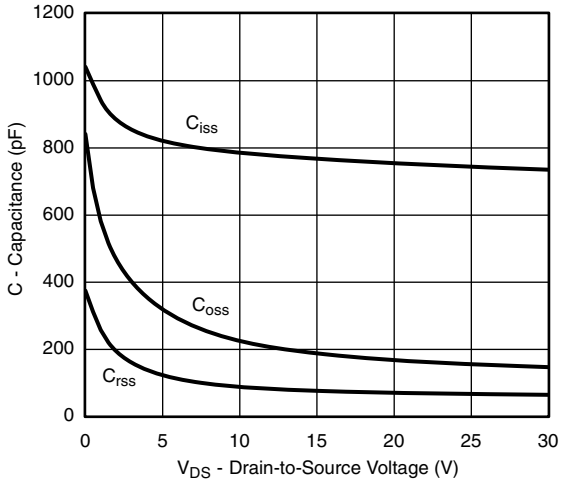
Output Characteristics



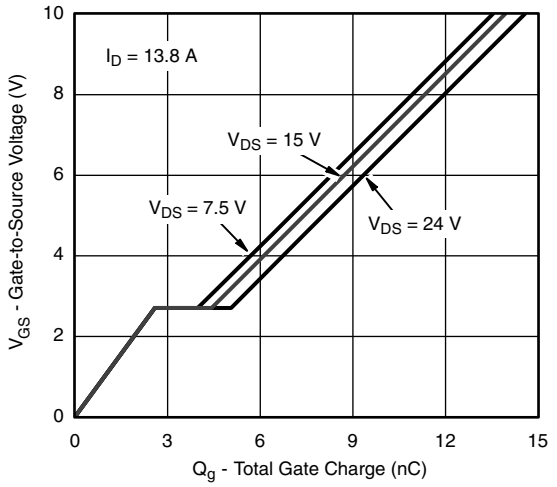
Transfer Characteristics



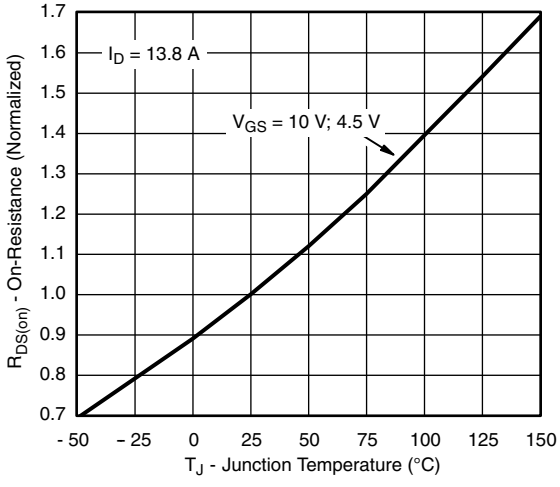
On-Resistance vs. Drain Current



Capacitance



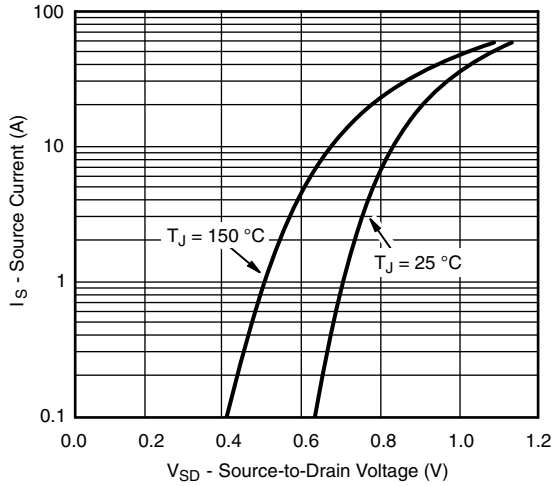
Gate Charge



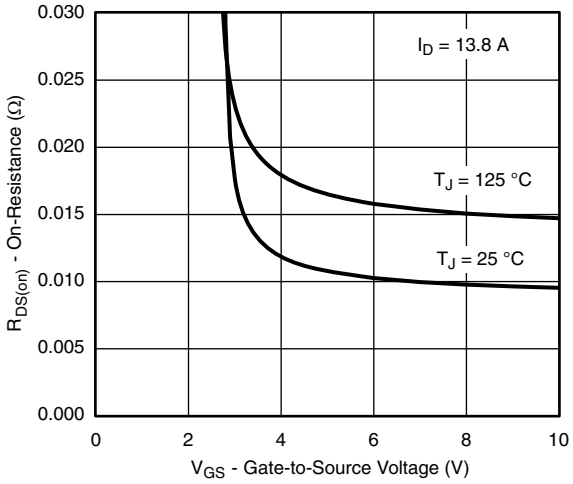
On-Resistance vs. Junction Temperature

For more information please contact: pmostechsupport@vishay.com
Document Number: 63783
S12-0543 Rev. A, 12-Mar-12

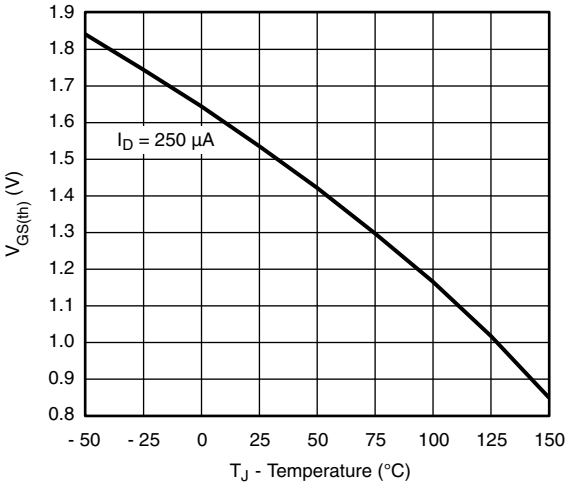
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



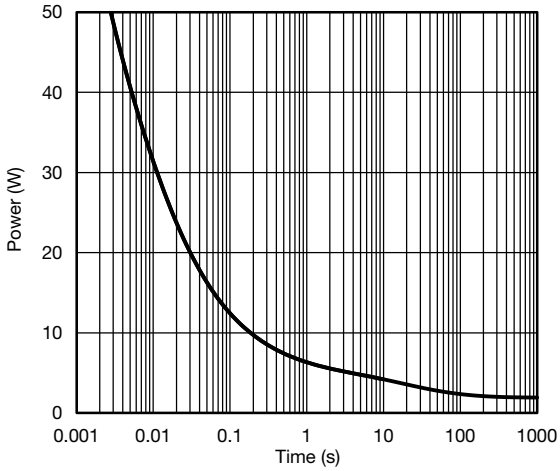
Source-Drain Diode Forward Voltage



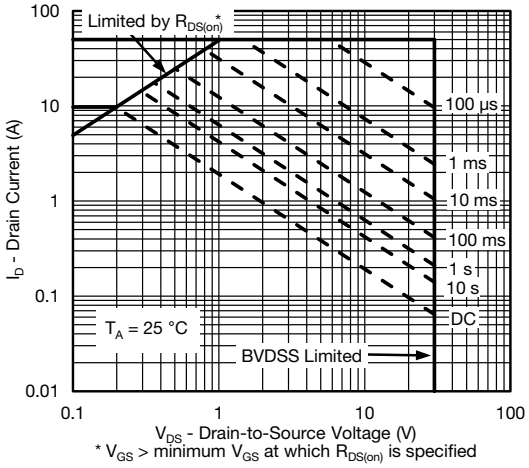
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

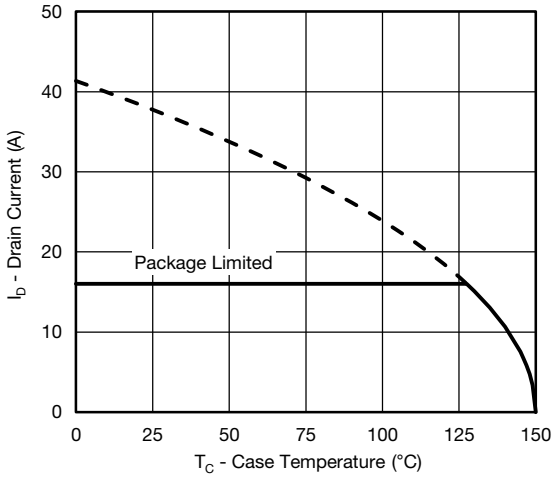


Single Pulse Power

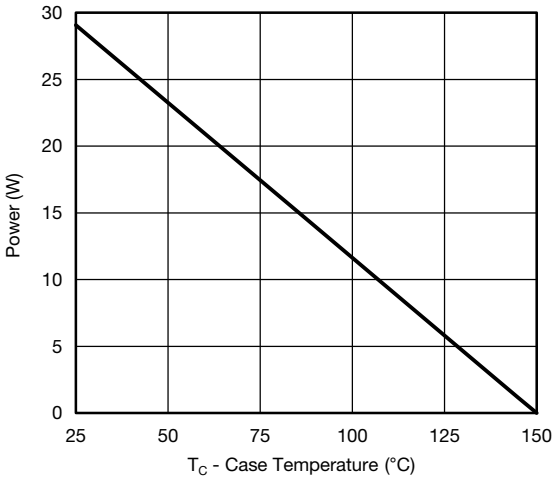


Safe Operating Area, Junction-to-Ambient

CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



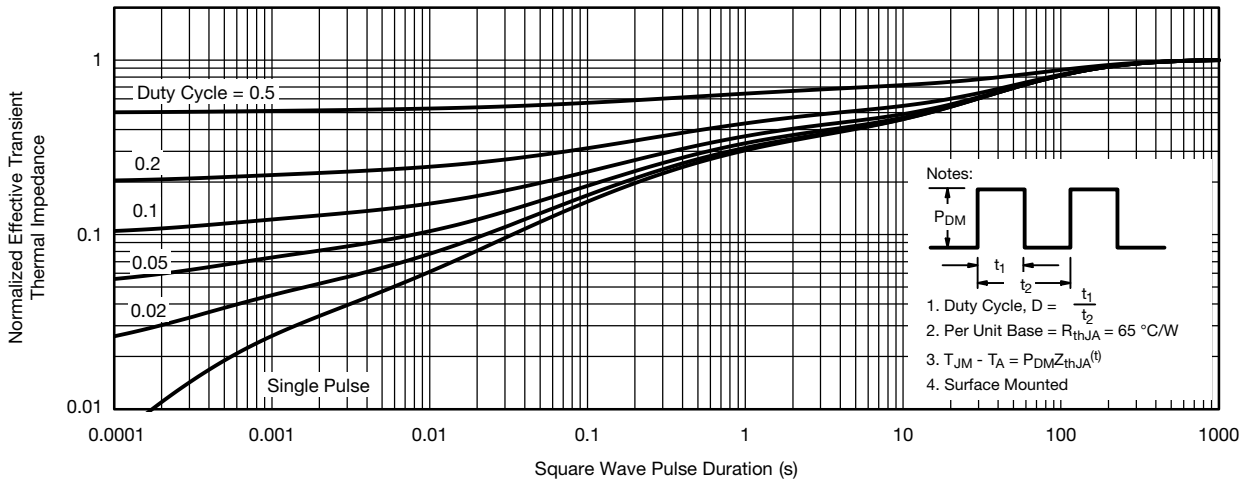
Current Derating*



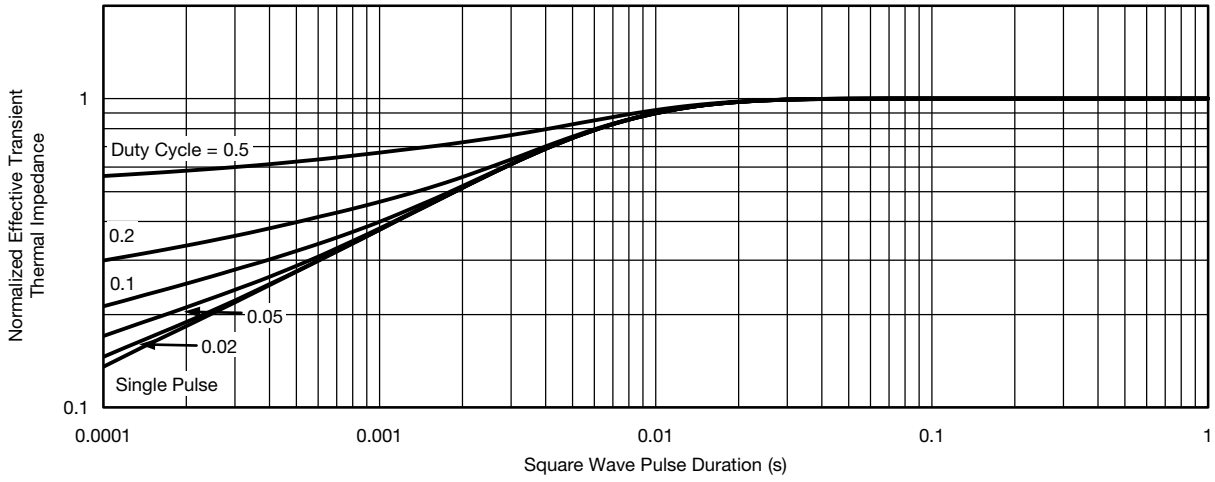
Power, Junction-to-Case

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

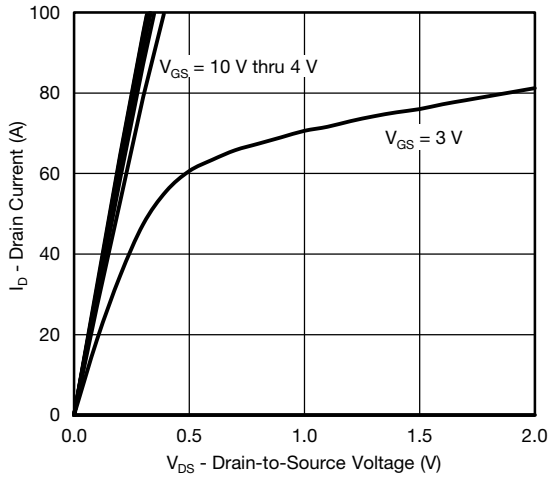


Normalized Thermal Transient Impedance, Junction-to-Ambient

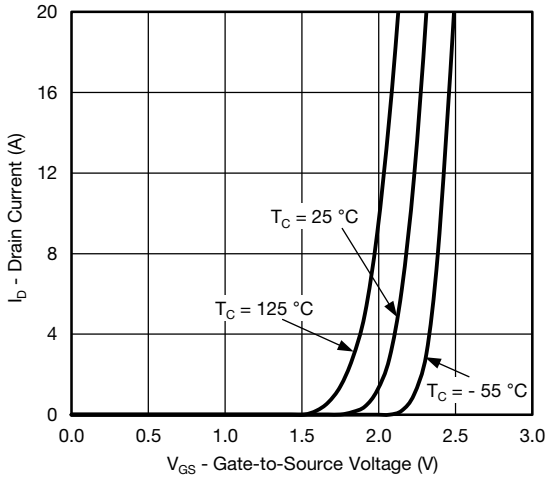


Normalized Thermal Transient Impedance, Junction-to-Case

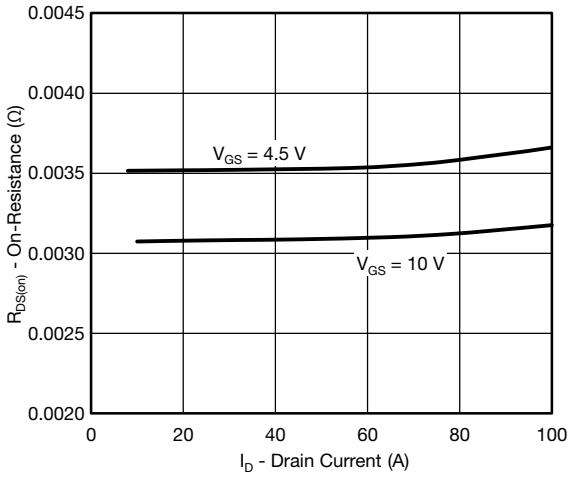
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



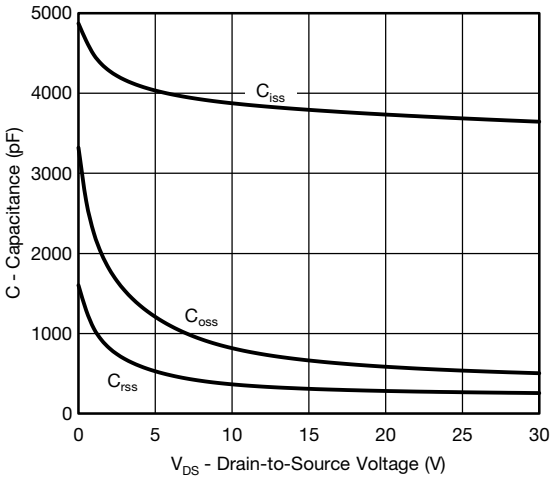
Output Characteristics



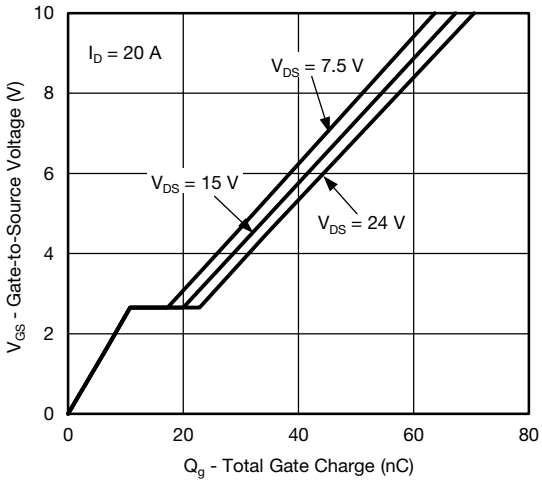
Transfer Characteristics



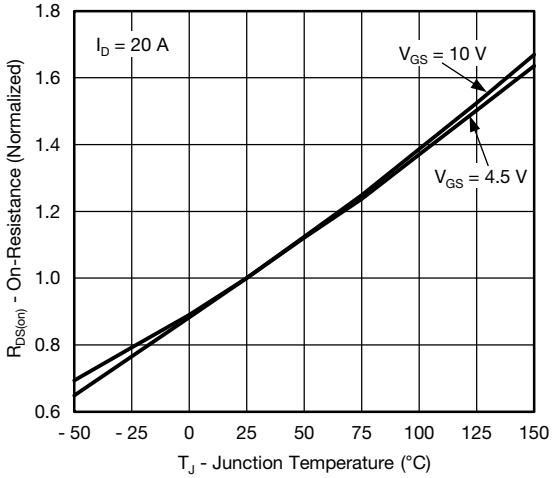
On-Resistance vs. Drain Current



Capacitance



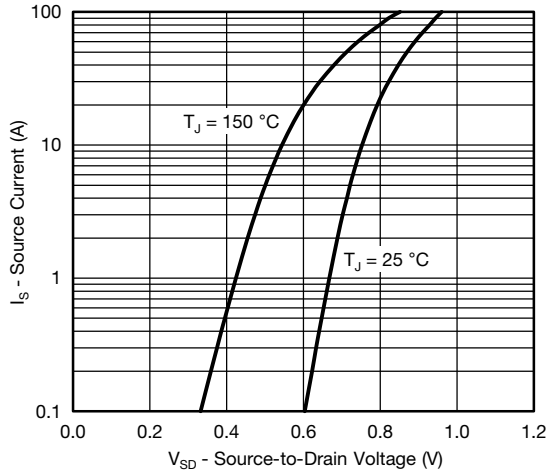
Gate Charge



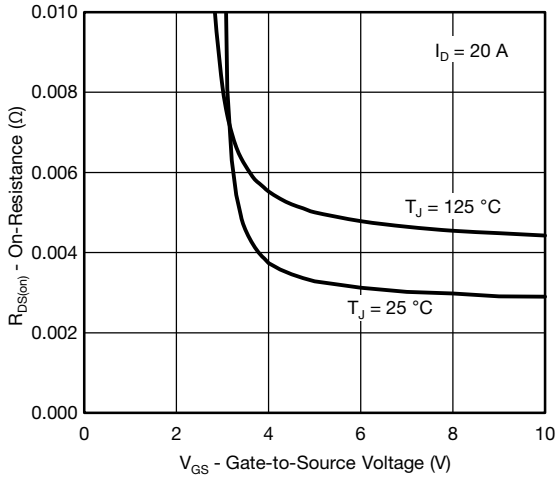
On-Resistance vs. Junction Temperature

For more information please contact: pmostechsupport@vishay.com
Document Number: 63783
S12-0543 Rev. A, 12-Mar-12

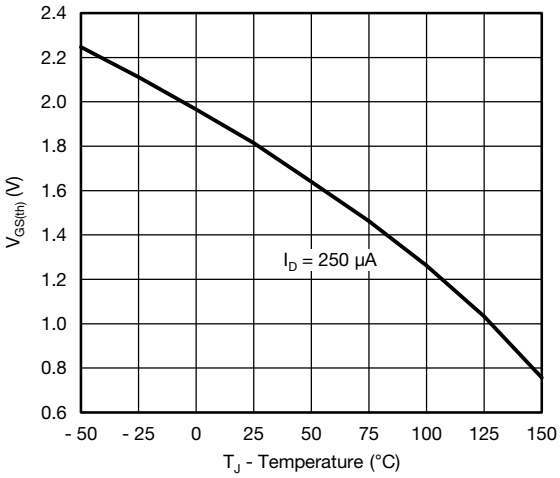
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



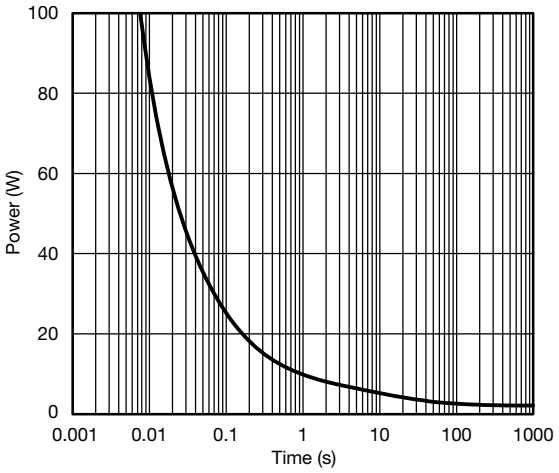
Source-Drain Diode Forward Voltage



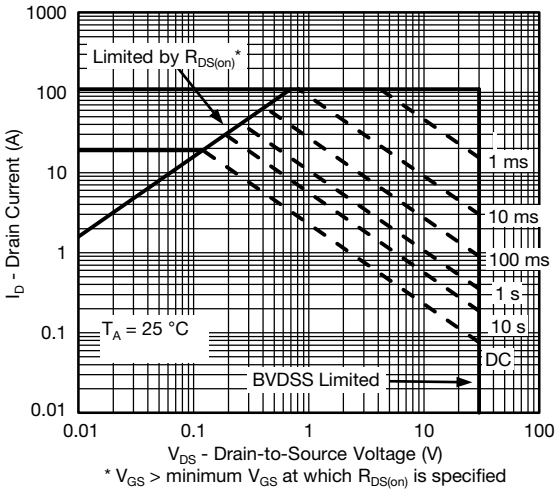
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



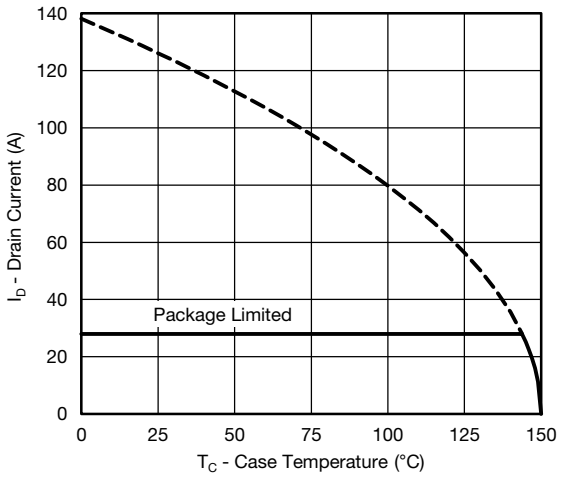
Single Pulse Power



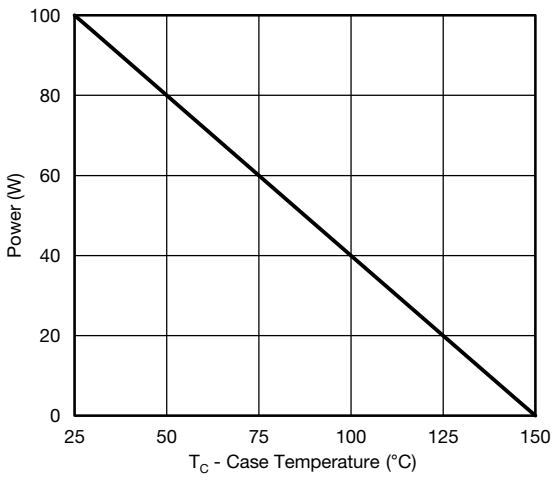
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



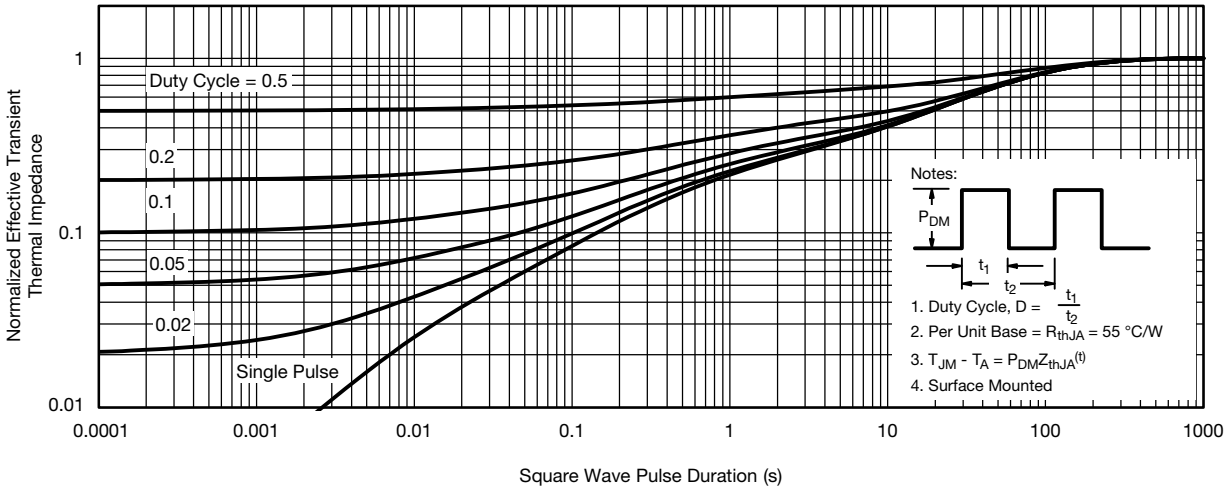
Current Derating*



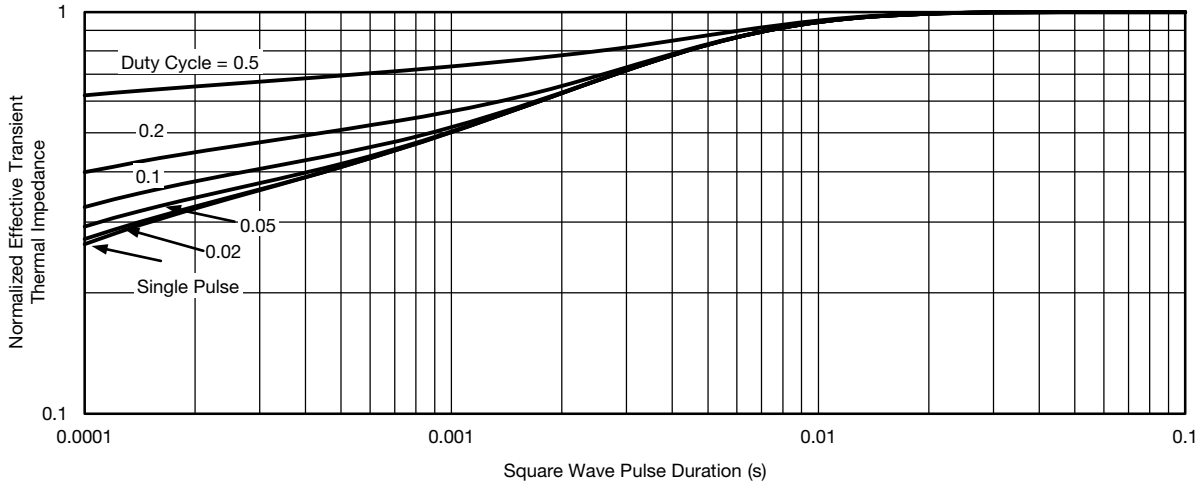
Power, Junction-to-Case

* The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



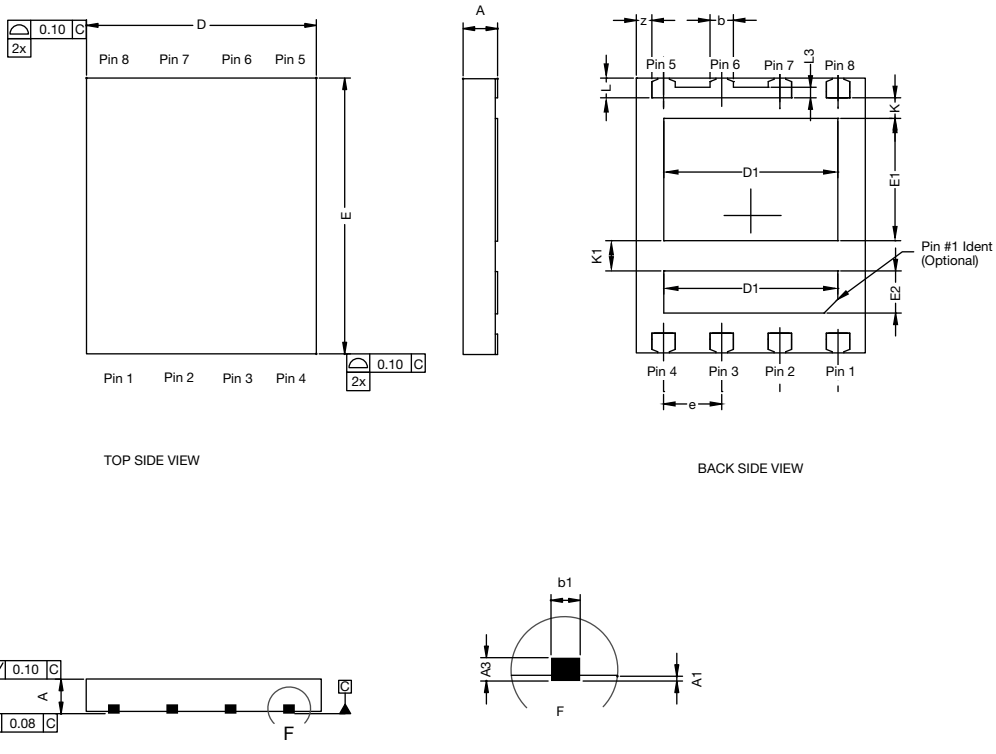
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

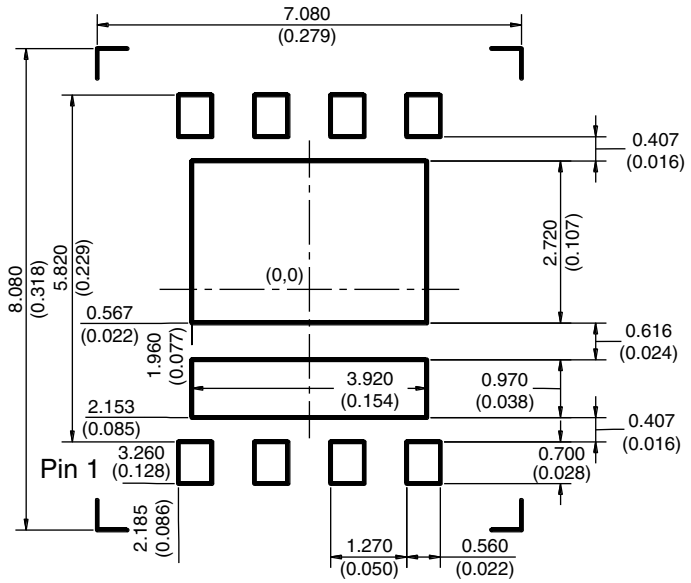
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63783.

PowerPAIR® 6 x 5 Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.75	0.80	0.028	0.030	0.032
A1	0.00	-	0.10	0.000	-	0.004
A3	0.20 REF			0.008 REF		
b	0.51 BSC			0.020 BSC		
b1	0.25 BSC			0.010 BSC		
D	5.00 BSC			0.197 BSC		
D1	3.75	3.80	3.85	0.148	0.150	0.152
E	6.00 BSC			0.236 BSC		
E1	2.62	2.67	2.72	0.103	0.105	0.107
E2	0.87	0.92	0.97	0.034	0.036	0.038
e	1.27 BSC			0.005 BSC		
K	0.45 TYP.			0.018 TYP.		
K1	0.66 TYP.			0.026 TYP.		
L	0.43 BSC			0.017 BSC		
L3	0.23 BSC			0.009 BSC		
z	0.34 BSC			0.013 BSC		
ECN: C11-1242-Rev. A, 07-Nov-11 DWG: 6005						

RECOMMENDED MINIMUM PAD FOR PowerPAIR® 6 x 5



Recommended Minimum Pad
Dimensions in mm (inches)

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay’s knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer’s responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer’s technical experts. Product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

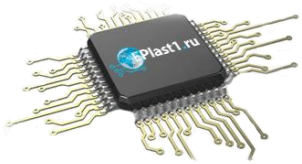
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)
Факс: 8 (812) 320-02-42
Электронная почта: org@eplast1.ru
Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.